

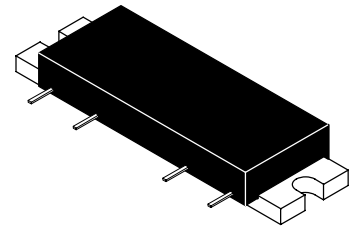
3G Band RF Linear LDMOS Amplifier

Designed for ultra-linear amplifier applications in 50 ohm systems operating in the 3G frequency band. A silicon FET Class A design provides outstanding linearity and gain. In addition, the excellent group delay and phase linearity characteristics are ideal for digital CDMA modulation systems.

- Third Order Intercept: 45 dBm Typ
- Power Gain: 31 dB Typ (@ f = 2140 MHz)
- Input VSWR \leq 1.5:1

Features

- Excellent Phase Linearity and Group Delay Characteristics
- Ideal for Feedforward Base Station Applications
- N Suffix Indicates Lead-Free Terminations

MHL21336N
**2110-2170 MHz
3.0 W, 31 dB
RF LINEAR LDMOS AMPLIFIER**

CASE 301AP-02, STYLE 1
Table 1. Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
DC Supply Voltage	V_{DD}	30	Vdc
RF Input Power	P_{in}	+5	dBm
Storage Temperature Range	T_{stg}	- 40 to +100	$^\circ\text{C}$
Operating Case Temperature Range	T_C	- 20 to +100	$^\circ\text{C}$

Table 2. Electrical Characteristics ($V_{DD} = 26$ Vdc, $T_C = 25^\circ\text{C}$; 50 Ω System)

Characteristic	Symbol	Min	Typ	Max	Unit
Supply Current	I_{DD}	—	500	525	mA
Power Gain (f = 2140 MHz)	G_p	30	31	33	dB
Gain Flatness (f = 2110 - 2170 MHz)	G_F	—	0.15	0.4	dB
Power Output @ 1 dB Compression (f = 2140 MHz)	P_{1dB}	34	35	—	dBm
Third Order Intercept (f1 = 2137 MHz, f2 = 2142 MHz)	ITO	44	45	—	dBm
Noise Figure (f = 2170 MHz)	NF	—	4.5	5	dB

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

TYPICAL CHARACTERISTICS

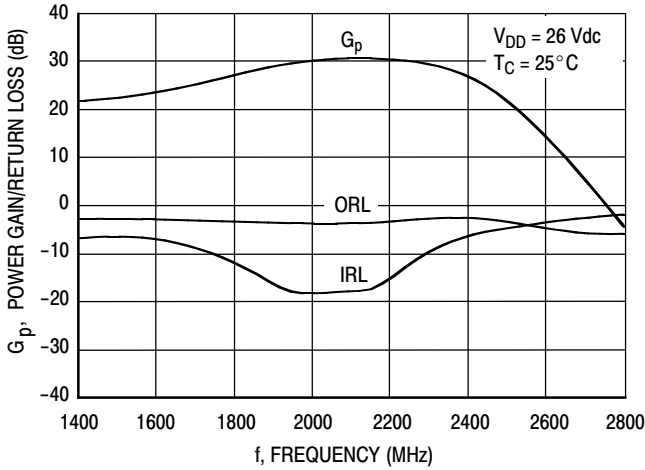


Figure 1. Power Gain, Input Return Loss, Output Return Loss versus Frequency

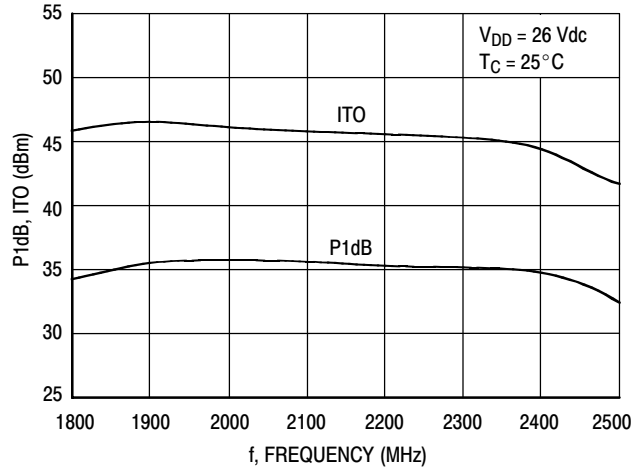


Figure 2. P1dB, ITO versus Frequency

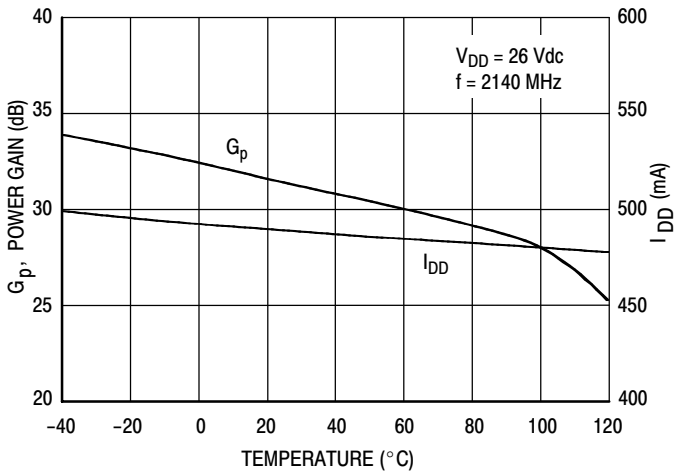


Figure 3. Power Gain, IDD versus Temperature

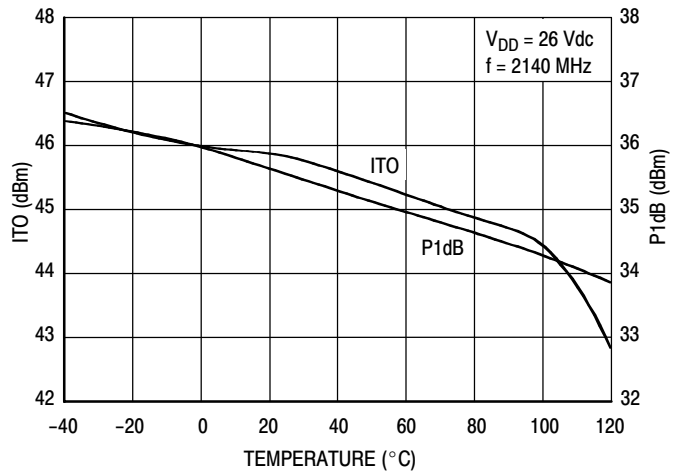


Figure 4. ITO, P1dB versus Temperature

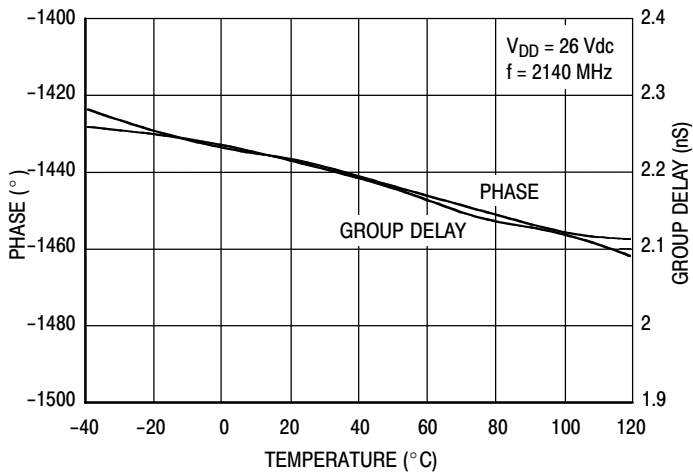


Figure 5. Phase⁽¹⁾, Group Delay⁽¹⁾ versus Temperature

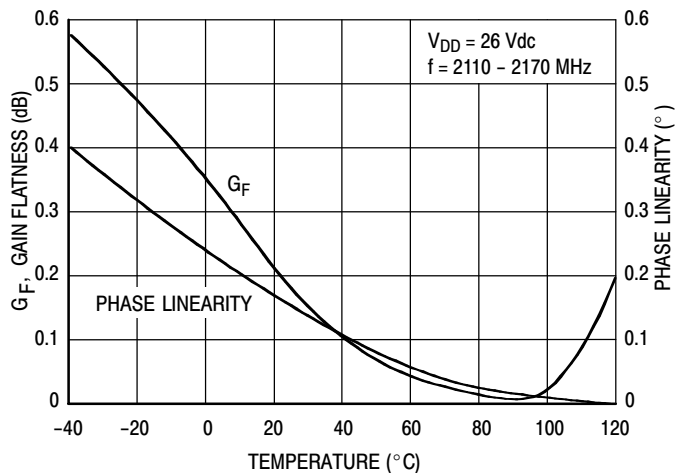


Figure 6. Gain Flatness, Phase Linearity versus Temperature

1. In Production Test Fixture

TYPICAL CHARACTERISTICS

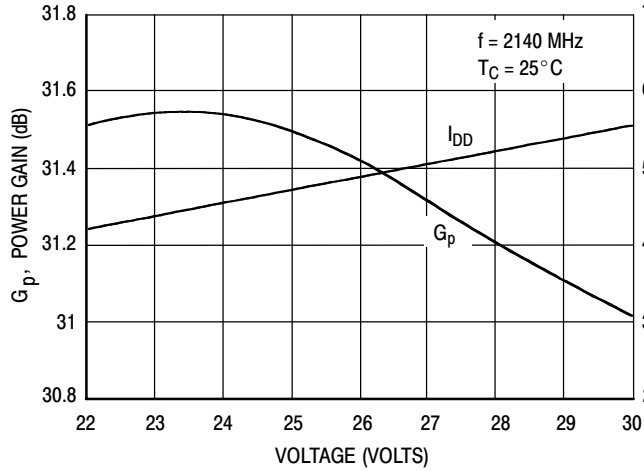


Figure 7. Power Gain, I_{DD} versus Voltage

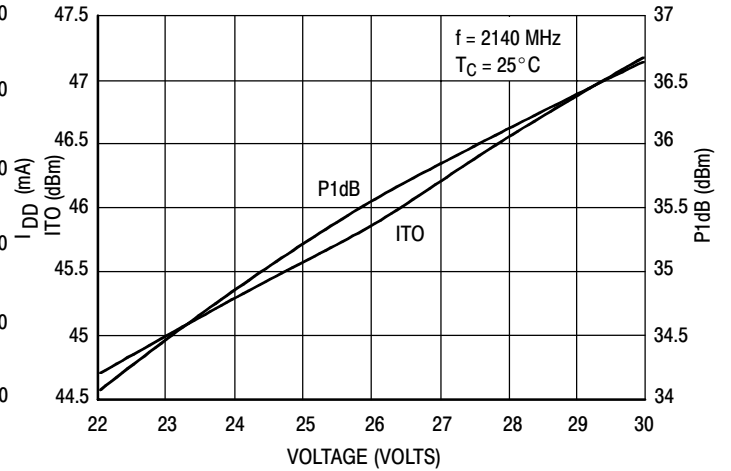


Figure 8. ITO, P1dB versus Voltage

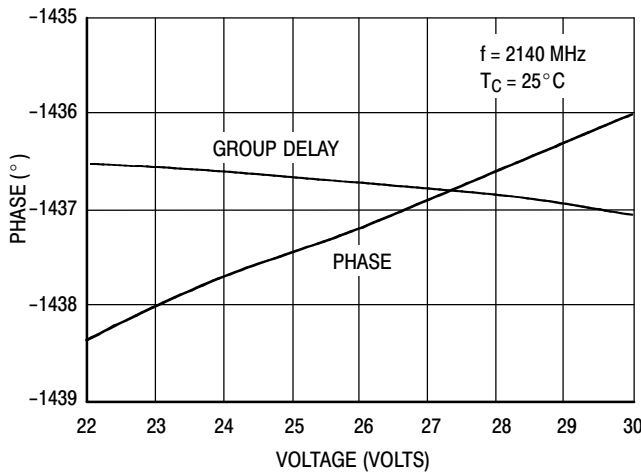


Figure 9. Phase⁽¹⁾, Group Delay⁽¹⁾ versus Voltage

1. In Production Test Fixture

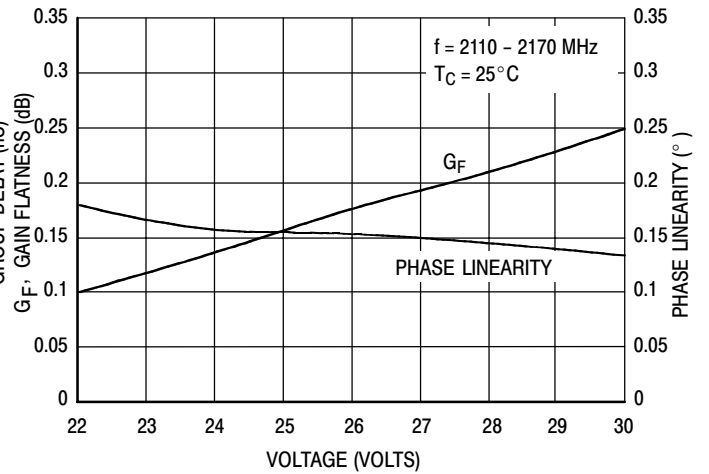
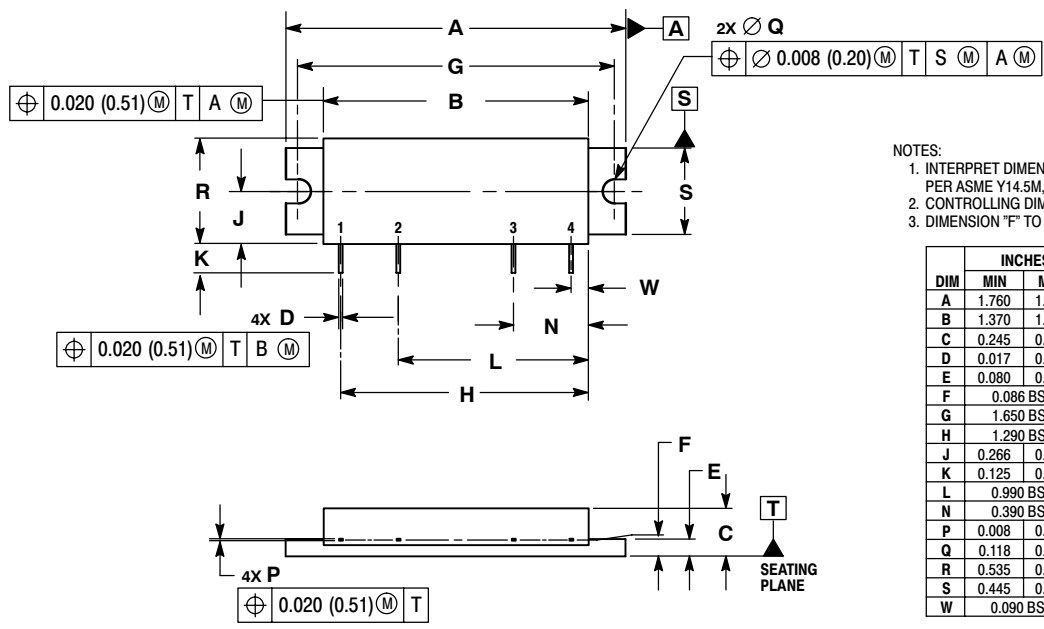


Figure 10. Phase Linearity, Gain Flatness versus Voltage

PACKAGE DIMENSIONS



- NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION "F" TO CENTER OF LEADS.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.760	1.780	44.70	45.21
B	1.370	1.390	34.80	35.31
C	0.245	0.265	6.22	6.73
D	0.017	0.023	0.43	0.58
E	0.080	0.100	2.03	2.54
F	0.086 BSC		2.18 BSC	
G	1.650 BSC		41.91 BSC	
H	1.290 BSC		32.77 BSC	
J	0.266	0.280	6.76	7.11
K	0.125	0.165	3.18	4.19
L	0.990 BSC		25.15 BSC	
N	0.390 BSC		9.91 BSC	
P	0.008	0.013	0.20	0.33
Q	0.118	0.132	3.00	3.35
R	0.535	0.555	13.59	14.10
S	0.445	0.465	11.30	11.81
W	0.090 BSC		2.29 BSC	

STYLE 1:
 PIN 1: RF INPUT
 2: VDD1
 3: VDD2
 4: RF OUTPUT
 CASE: GROUND

CASE 301AP-02 ISSUE E

How to Reach Us:

Home Page:

www.freescale.com

E-mail:

support@freescale.com

USA/Europe or Locations Not Listed:

Freescale Semiconductor
 Technical Information Center, CH370
 1300 N. Alma School Road
 Chandler, Arizona 85224
 +1-800-521-6274 or +1-480-768-2130
support@freescale.com

Europe, Middle East, and Africa:

Freescale Halbleiter Deutschland GmbH
 Technical Information Center
 Schatzbogen 7
 81829 Muenchen, Germany
 +44 1296 380 456 (English)
 +46 8 52200080 (English)
 +49 89 92103 559 (German)
 +33 1 69 35 48 48 (French)
support@freescale.com

Japan:

Freescale Semiconductor Japan Ltd.
 Headquarters
 ARCO Tower 15F
 1-8-1, Shimo-Meguro, Meguro-ku,
 Tokyo 153-0064
 Japan
 0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:

Freescale Semiconductor Hong Kong Ltd.
 Technical Information Center
 2 Dai King Street
 Tai Po Industrial Estate
 Tai Po, N.T., Hong Kong
 +800 2666 8080
support.asia@freescale.com

For Literature Requests Only:

Freescale Semiconductor Literature Distribution Center
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